

RELIABILITY REPORT  
FOR  
MAX3395EEUD+  
(MAX3394E/MAX3395E/MAX3396E)  
PLASTIC ENCAPSULATED DEVICES

April 13, 2009

**MAXIM INTEGRATED PRODUCTS**

120 SAN GABRIEL DR.  
SUNNYVALE, CA 94086

<b>Approved by</b>
Ken Wendel
Quality Assurance
Director, Reliability Engineering

## Conclusio

The MAX3395EEUD+ successfully meets the quality and reliability standards required of all Maxim products. In addition, Maxim's continuous reliability monitoring program ensures that all outgoing product will continue to meet Maxim's quality and reliability standards.

## Table of Contents

<b>I. ....Device Description</b>	<b>V. ....Quality Assurance Information</b>
<b>II. ....Manufacturing Information</b>	<b>VI. ....Reliability Evaluation</b>
<b>III. ....Packaging Information</b>	<b>IV. ....Die Information</b>
<b>.....Attachments</b>	

### I. Device Description

#### A. General

The MAX3394E/MAX3395E/MAX3396E bidirectional level translators provide level shifting required for data transfer in a multivoltage system. Internal slew-rate enhancement circuitry features 10mA current-sink and 15mA current-source drivers to isolate capacitive loads from lower current drivers. In open-drain systems, slew-rate enhancement enables fast data rates with larger pullup resistors and increased bus load capacitance. Externally applied voltages, VCC and VL, set the logic-high levels for the device. A logic-low signal on one I/O side of the device appears as a logic-low signal on the opposite I/O side, and vice-versa. Each I/O line is pulled up to VCC or VL by an internal pullup resistor, allowing the devices to be driven by either push-pull or open-drain drivers.

The MAX3394E/MAX3395E/MAX3396E feature a tri-state output mode, thermal-shutdown protection, and  $\pm 15\text{kV}$  Human Body Model (HBM) ESD protection on the VCC side for greater protection in applications that route signals externally.

The MAX3394E/MAX3395E/MAX3396E accept VCC voltages from +1.65V to +5.5V, and VL voltages from +1.2V to VCC, making them ideal for data transfer between low voltage ASIC/PLDs and higher voltage systems. The MAX3394E/MAX3395E/MAX3396E operate at a guaranteed data rate of 6Mbps with push-pull drivers and 1Mbps with open-drain drivers.

The MAX3394E is a dual-level translator available in 9-bump UCSP™ and 8-pin 3mm x 3mm TDFN packages. The MAX3395E is a quad-level translator available in 12-bump UCSP, and 12-pin 4mm x 4mm TQFN packages. The MAX3396E is an octal-level translator available in 20-bump UCSP and 20-pin 5mm x 5mm TQFN packages. The MAX3394E/MAX3395E/MAX3396E operate over the extended -40°C to +85°C temperature range.

## II. Manufacturing Information

A. Description/Function:	±15kV ESD-Protected, High-Drive Current, Dual-/Quad-/Octal-Level Translators with Speed-Up Circuitry
B. Process:	B6
C. Number of Device Transistors:	
D. Fabrication Location:	California
E. Assembly Location:	ATP Philippines, UTL Thailand, Carsem Malaysia
F. Date of Initial Production:	January 21, 2006

## III. Packaging Information

A. Package Type:	14-pin TSSOP
B. Lead Frame:	Copper
C. Lead Finish:	100% matte Tin
D. Die Attach:	Conductive Epoxy
E. Bondwire:	Au (1.0 mil dia.)
F. Mold Material:	Epoxy with silica filler
G. Assembly Diagram:	#
H. Flammability Rating:	Class UL94-V0
I. Classification of Moisture Sensitivity per JEDEC standard J-STD-020-C	Level 1
J. Single Layer Theta Ja:	110°C/W
K. Single Layer Theta Jc:	30°C/W
L. Multi Layer Theta Ja:	100.4°C/W
M. Multi Layer Theta Jc:	30°C/W

## IV. Die Information

A. Dimensions:	80 X 61 mils
B. Passivation:	Si <sub>3</sub> N <sub>4</sub> /SiO <sub>2</sub> (Silicon nitride/ Silicon dioxide)
C. Interconnect:	Aluminum/Cu (Cu = 0.5%)
D. Backside Metallization:	None
E. Minimum Metal Width:	0.6 microns (as drawn)
F. Minimum Metal Spacing:	0.6 microns (as drawn)
G. Bondpad Dimensions:	5 mil. Sq.
H. Isolation Dielectric:	SiO <sub>2</sub>
I. Die Separation Method:	Wafer Saw

## V. Quality Assurance Information

A. Quality Assurance Contacts:	Ken Wendel (Director, Reliability Engineering) Bryan Preeshl (Managing Director of QA)
B. Outgoing Inspection Level:	0.1% for all electrical parameters guaranteed by the Datasheet. 0.1% For all Visual Defects.
C. Observed Outgoing Defect Rate:	< 50 ppm
D. Sampling Plan:	Mil-Std-105D

## VI. Reliability Evaluation

### A. Accelerated Life Test

The results of the 135°C biased (static) life test are shown in Table 1. Using these results, the Failure Rate ( $\lambda$ ) is calculated as follows:

$$\lambda = \frac{1}{\text{MTTF}} = \frac{1.83}{192 \times 4340 \times 45 \times 2} \quad (\text{Chi square value for MTTF upper limit})$$

(where 4340 = Temperature Acceleration factor assuming an activation energy of 0.8eV)

$$\lambda = 23.9 \times 10^{-9}$$

$$\lambda = 23.9 \text{ F.I.T. (60\% confidence level @ 25°C)}$$

The following failure rate represents data collected from Maxim's reliability monitor program. Maxim performs quarterly 1000 hour life test monitors on its processes. This data is published in the Product Reliability Report found at <http://www.maxim-ic.com/>. Current monitor data for the B6 Process results in a FIT Rate of 0.8 @ 25C and 14.2 @ 55C (0.8 eV, 60% UCL)

### B. Moisture Resistance Tests

The industry standard 85°C/85%RH or HAST testing is monitored per device process once a quarter.

### C. E.S.D. and Latch-Up Testing

The RT96 die type has been found to have all pins able to withstand a HBM transient pulse of +/-1000 V per JEDEC JESD22-A114-D. Latch-Up testing has shown that this device withstands a current of +/-250 mA.

**Table 1**  
Reliability Evaluation Test Results

**MAX3395EEUD+**

TEST ITEM	TEST CONDITION	FAILURE IDENTIFICATION	SAMPLE SIZE	NUMBER OF FAILURES
<b>Static Life Test</b> (Note 1)	Ta = 135°C Biased Time = 192 hrs.	DC Parameters & functionality	45	0
<b>Moisture Testing</b> (Note 2) 85/85	Ta = 85°C RH = 85% Biased Time = 1000hrs.	DC Parameters & functionality	77	0
<b>Mechanical Stress</b> (Note 2) Temperature Cycle	-65°C/150°C 1000 Cycles Method 1010	DC Parameters & functionality	77	0

Note 1: Life Test Data may represent plastic DIP qualification lots.

Note 2: Generic Package/Process data